Product data sheet

1. General description

Dual ultrafast power diode in a SOT1259 (3-lead TO-3P) plastic package.

2. Features and benefits

- · Very low on-state loss
- Fast switching
- · Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- · High thermal cycling performance
- · Low thermal resistance

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|-------------------------------------|---|---|-----|------|------|------|
| V_R | reverse voltage | DC | | - | - | 200 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _{mb} ≤ 119 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | | - | - | 15 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4 | | - | - | 200 | A |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | - | - | 220 | A | |
| Static characte | eristics | | | | | | |
| V_{F} | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 1 | 1.2 | V |
| | | I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 0.95 | 1.05 | V |
| | | I _F = 15 A; T _j = 150 °C | | - | 0.78 | 0.9 | V |
| Dynamic chara | acteristics | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $Fig. 7$ | | - | 18 | 25 | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | A1 | anode 1 | | A1 A2 |
| 2 | K | cathode | 10 O o/ | A1 |
| 3 | A2 | anode 2 | | K sym125 |
| mb | mb | mounting base; connected to cathode | TO3P (SOT1259) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | |
|-------------|---------|--|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| BYQ72EK-200 | ТОЗР | Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO3P | SOT1259 | | | | |

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 200 | V |
| V_{RWM} | crest working reverse voltage | | - | 200 | V |
| V_R | reverse voltage | DC | - | 200 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _{mb} ≤ 119 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | - | 15 | Α |
| I _{O(AV)} | average output current | δ = 0.5 ; T _{mb} ≤ 119 °C; square-wave pulse; both diodes conducting | - | 30 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4 | - | 200 | Α |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | - | 220 | Α |
| I _{RRM} | repetitive peak reverse current | t_p = 2 μ s; δ = 0.001; per diode | - | 0.2 | Α |
| I _{RSM} | non-repetitive peak reverse current | $t_p = 100 \ \mu s$; per diode | - | 0.2 | Α |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |
| Electrostation | c discharge | | | | |
| V_{ESD} | electrostatic discharge voltage | C = 250 pF; R = 1.5 kΩ; HBM | - | 8 | V |

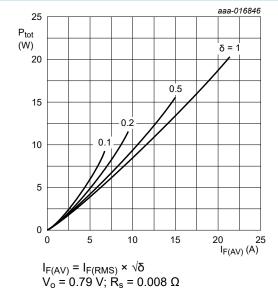


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

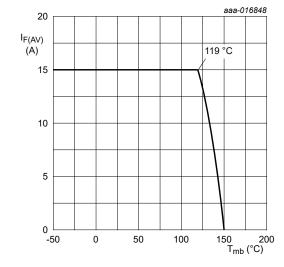


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

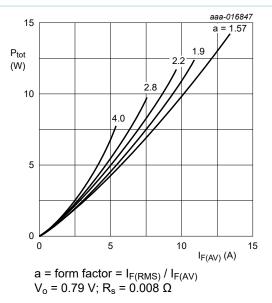


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

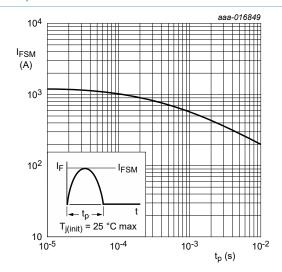


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|--|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | with heatsink compound; per diode; Fig. 5 | - | 1.1 | 2 | K/W |
| | | with heatsink compound; both diodes conducting | - | 0.7 | 1.2 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | _ | 45 | - | K/W |

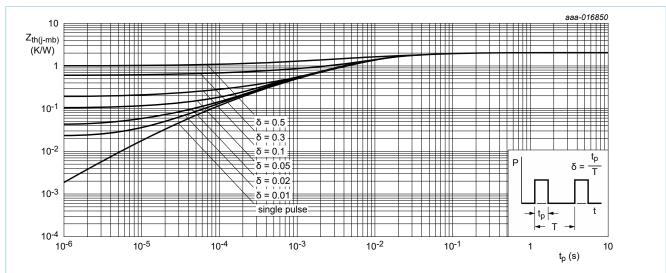


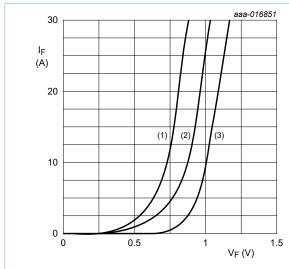
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode; maximum values

9. Characteristics

Table 6. Characteristics

characteristics are per diode unless otherwise stated

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------|-------------------------------|---|--|-----|------|------|------|
| Static chara | acteristics | | | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 1 | 1.2 | V |
| | | I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u> | | - | 0.95 | 1.05 | V |
| | | I _F = 15 A; T _j = 150 °C | | - | 0.78 | 0.9 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | | - | 3 | 20 | μΑ |
| | | V _R = 600 V; T _j = 100 °C | | - | 0.3 | 1 | mA |
| Dynamic ch | naracteristics | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | | - | 18 | 25 | ns |
| I _{RM} | peak reverse recovery current | | | - | 1 | - | Α |
| Q _r | recovered charge | $I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $Fig. 7$ | | - | 6 | 15 | nC |
| | | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 7}}{}$ | | - | 10 | - | nC |
| V_{FR} | forward recovery voltage | $I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 8 | | - | 1 | - | V |



 V_o = 0.79 V; R_s = 0.008 Ω

(1) Tj = 150 °C; typical values

(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values



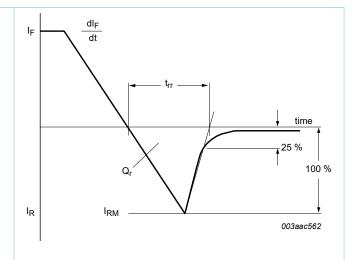
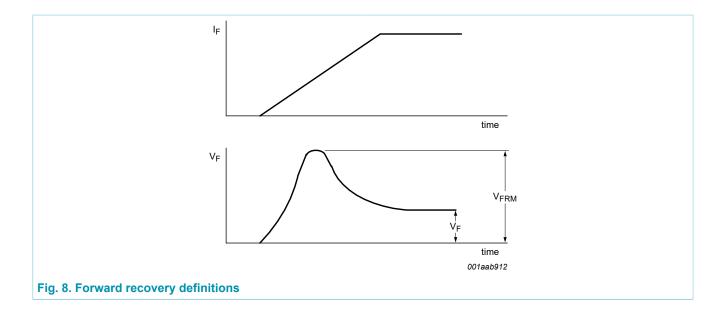


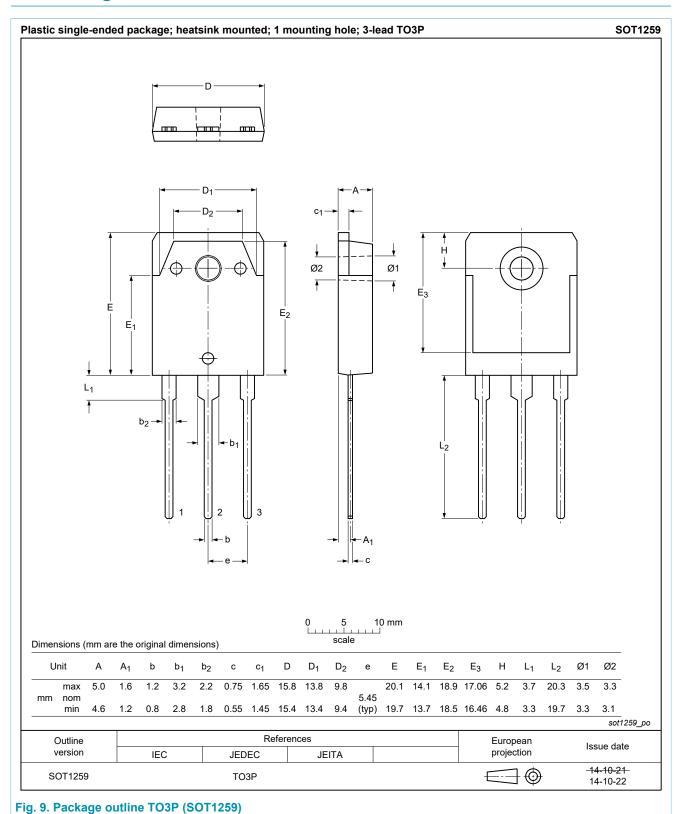
Fig. 7. Reverse recovery definitions; ramp recovery

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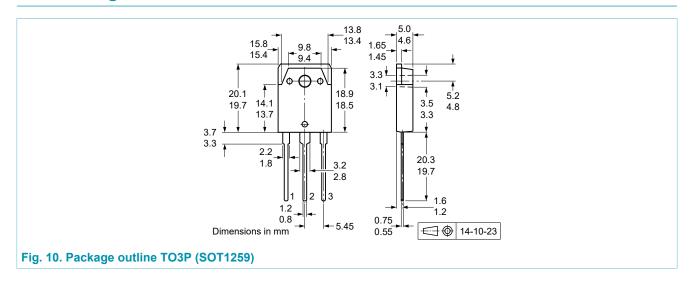
Dual ultrafast power diode



10. Package outline



11. Package outline



12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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